

### SOT-89-3L Plastic-Encapsulate Transistors

#### S9014U TRANSISTOR (NPN)

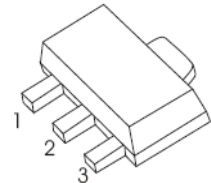
#### FEATURES

- Complementary to S9015U

MARKING: J6

#### SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



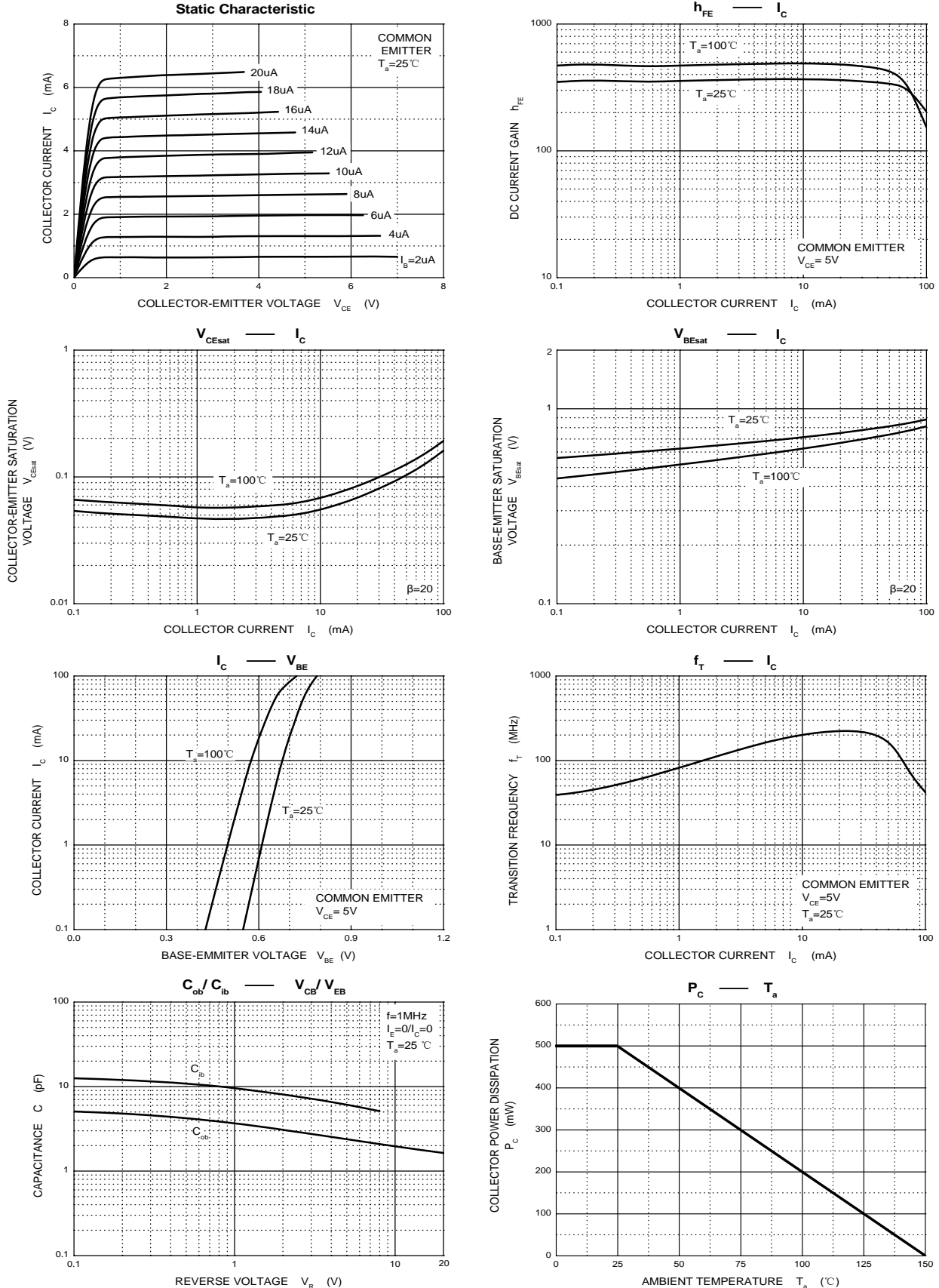
#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	50	V
$V_{CE0}$	Collector-Emitter Voltage	45	V
$V_{EB0}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	100	mA
$P_C$	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

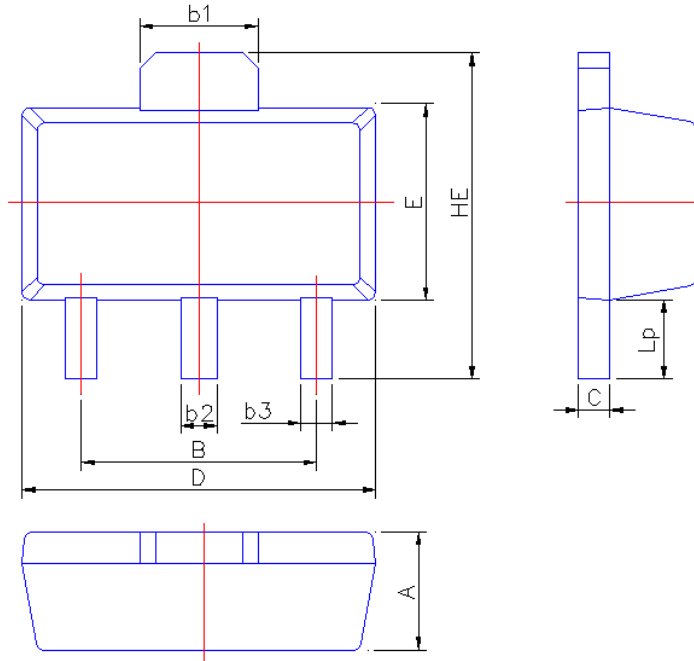
#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=50\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=35\text{V}, I_B=0$			1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=3\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=5\text{V}, I_C=1\text{mA}$	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=5\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=10\text{mA}$ $f=30\text{MHz}$	150			MHz

## Typical Characteristics



### SOT-89 PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	1.40	1.60
B	2.95	3.05
b1	1.45	1.70
b2	0.45	0.56
b3	0.35	0.50
C	0.35	0.50
D	4.40	4.60
E	2.35	2.55
HE	3.90	4.40
Lp	0.90	1.10